

Supplement #1: October 27, 2001

Logic Circuit Supplement

A) Transistor Inverter Example

B) Terminology and Using $V_{\text{OUT-SAT-D}}$

C) States are Voltage Levels of V_{IN}

D) Single Equation I_{OUT} vs. V_{OUT}

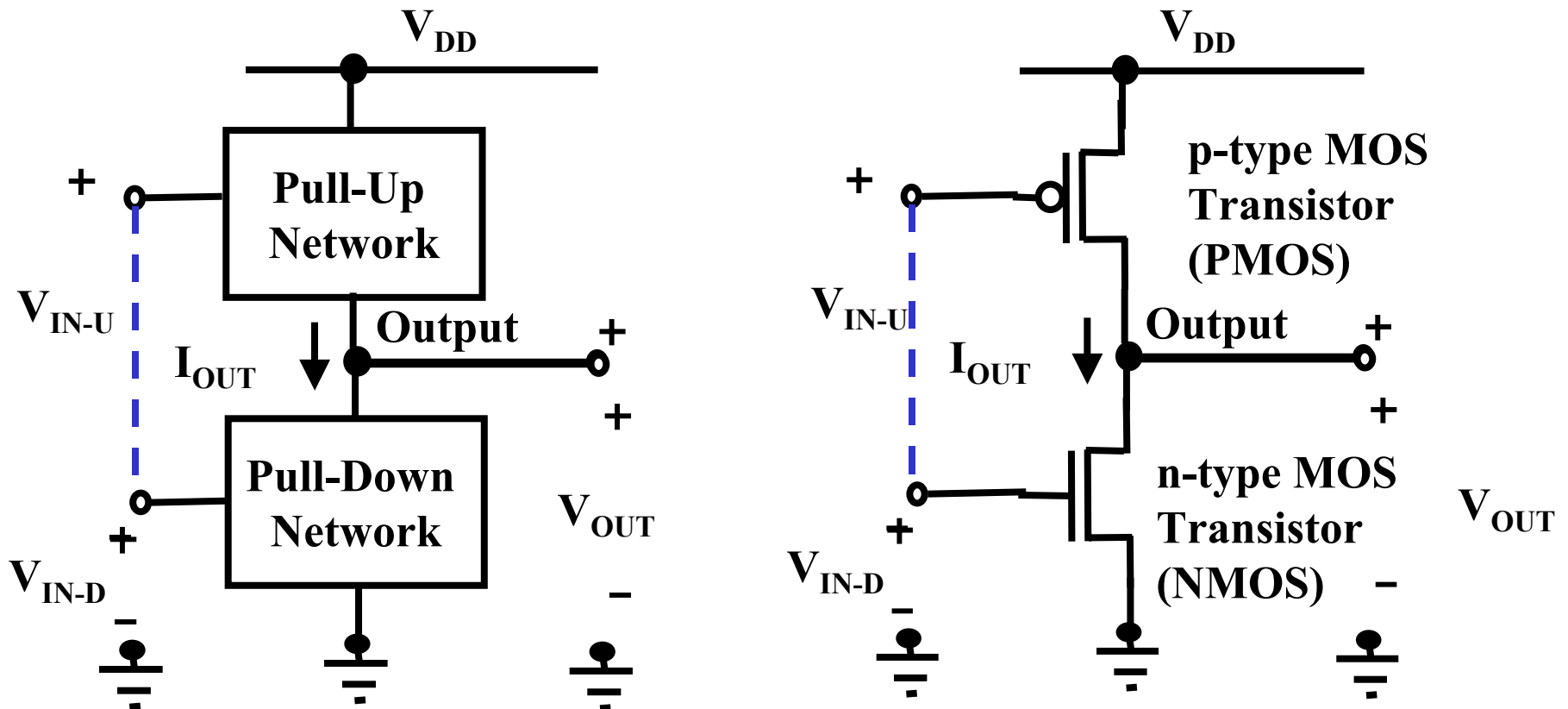
E) Composite I_{OUT} vs. V_{OUT} for $R_{\text{PULL-UP}}$

F) Composite I_{OUT} vs. V_{OUT} for Active
Pull-Up

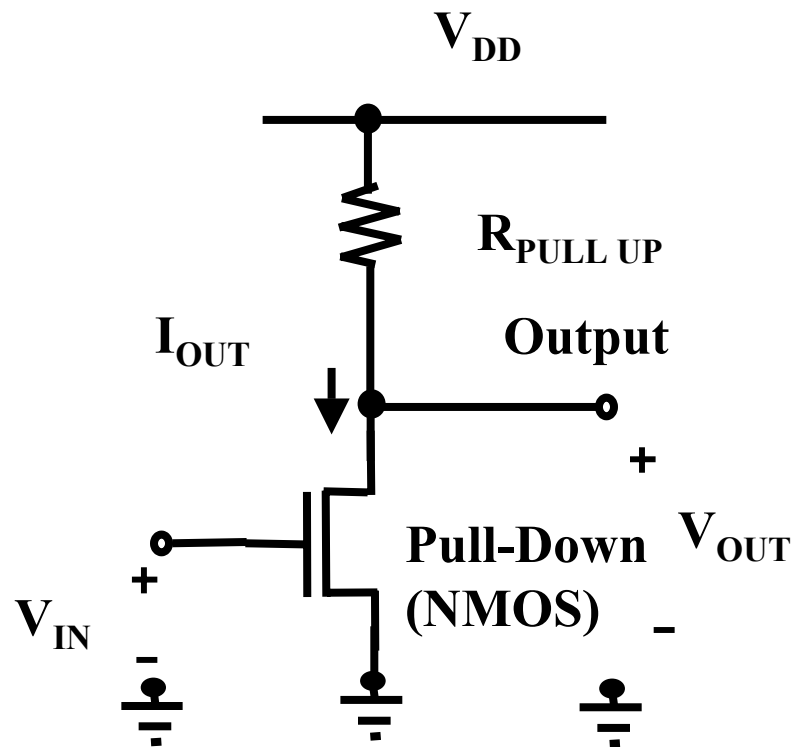
G) Voltage Transfer Function and V_{M}

Transistor Inverter Example

It may be simpler to just **think of PMOS and NMOS transistors** instead of a general 3 terminal pull-up or pull-down device.



Terminology



V_{DD} = Power supply voltage

Pull-Down Device = Device used to carry current from the output node to ground to discharge the output node to ground.

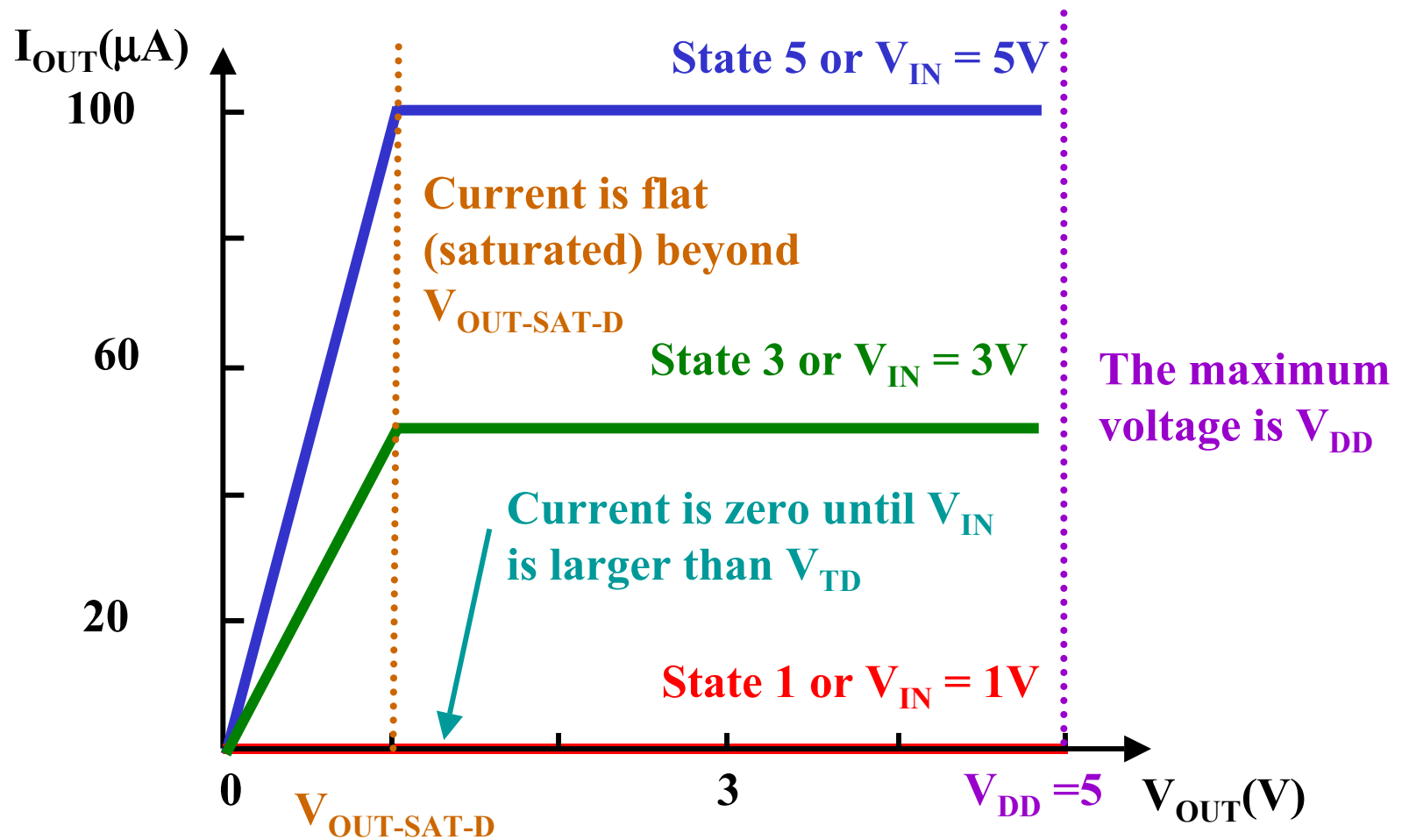
Pull-Up Device = Device used to carry current from the power supply to the output node to charge the output node to the power supply voltage.

I_{OUT} = Current into the pull down device

V_{TD} = Value of V_{IN} at which the **NMOS** transistor begins to conduct.

$V_{\text{OUT-SAT-D}}$ = Value of V_{OUT} beyond which the current I_{OUT} no longer increases in the NMOS.

States are Voltage Levels of V_{IN}



Eliminating Point of Confusion

The use of V_{TD} twice in the equation for I_{OUT} is confusing (although it eliminates an extra parameter).

$$I_{OUT-PD} = k_D (V_{IN} - V_{TD}) V_{TD}$$

Instead we add an extra parameter to distinguish between threshold for conduction which is determined by V_{IN} reaching V_{TD} and saturation of the current level when V_{OUT} reaches $V_{OUT-SAT-D}$.

$$I_{OUT-PD} = k_D (V_{IN} - V_{TD}) V_{OUT-SAT-D}$$

Single Equation EE42 NMOS Model

Current I_{OUT} only flows when V_{IN} is larger than the threshold value V_{TD} and the current is proportional to V_{OUT} up to $V_{OUT-SAT-D}$ where it reaches

$$I_{OUT-PD} = k_D (V_{IN} - V_{TD}) V_{OUT-SAT-D}$$

Note that we have added an extra parameter to distinguish between threshold (V_{TD}) and saturation ($V_{OUT-SAT-D}$).

Example:

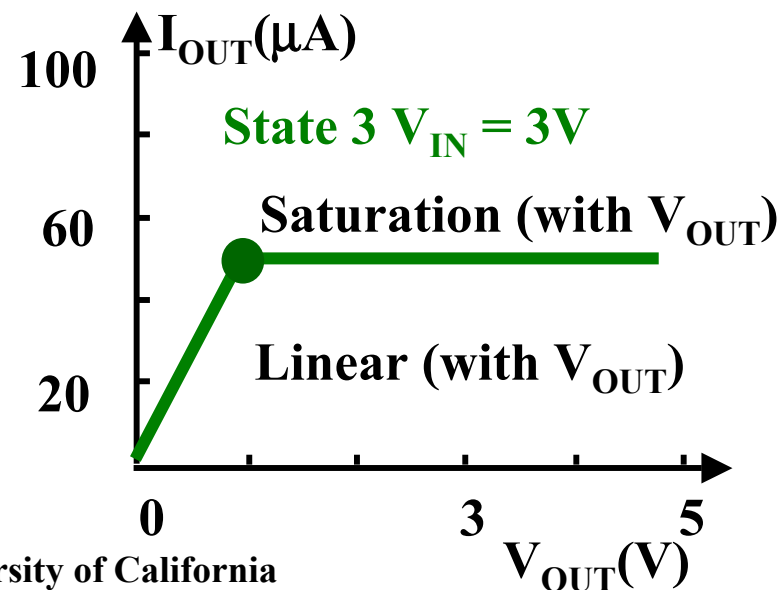
$$k_D = 25 \mu\text{A}/\text{V}^2$$

$$V_{TD} = 1\text{V}$$

$$V_{OUT-SAT-D} = 1\text{V}$$

Use these
values in the
homework.

$$I_{OUT-PD} = 25 \frac{\mu\text{A}}{\text{V}^2} (3\text{V} - 1\text{V}) 1\text{V} = 50 \mu\text{A}$$



Single Equation EE42 PMOS Model

Current I_{OUT} only flows when V_{IN} is smaller than V_{DD} minus the threshold value V_{TU} and the current is proportional to $(V_{DD}-V_{OUT})$ up to $(V_{DD}-V_{OUT-SAT-U})$ where it reaches

$$I_{OUT-PU} = k_U (V_{DD} - V_{IN} - V_{TU}) V_{OUT-SAT-U}$$

Example:

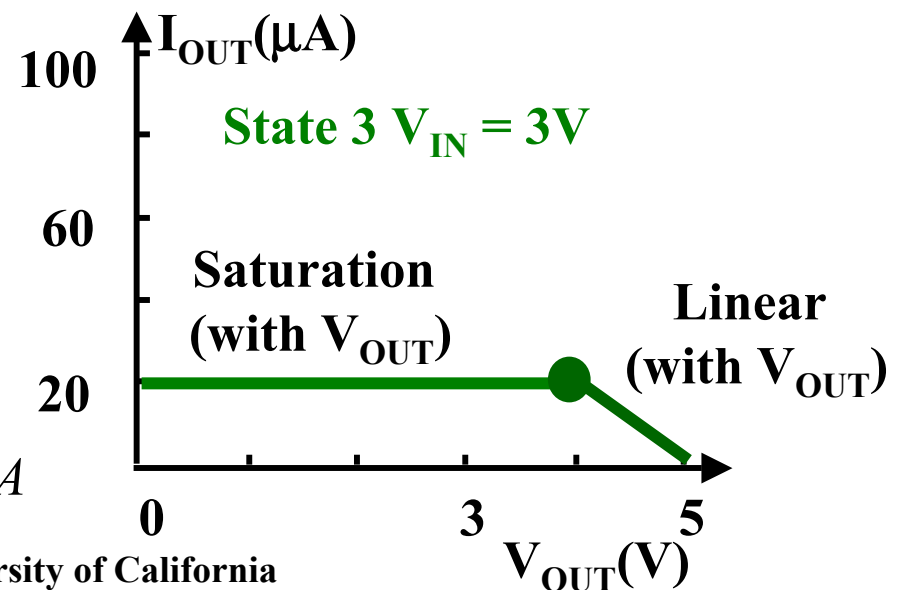
$$k_U = 20 \mu A/V^2$$

$$V_{TU} = 1V$$

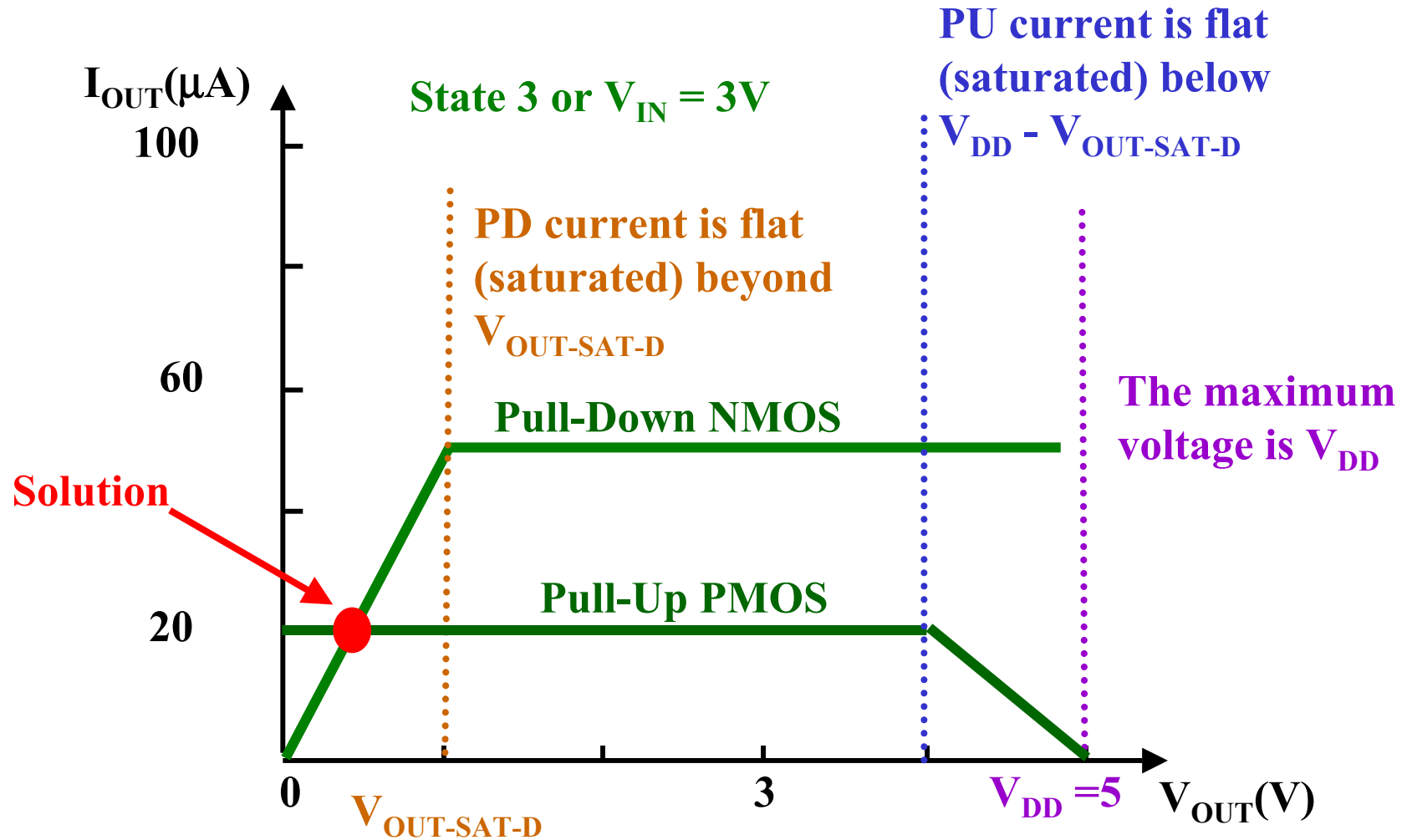
$$V_{OUT-SAT-u} = 1V$$

Use these values in the homework.

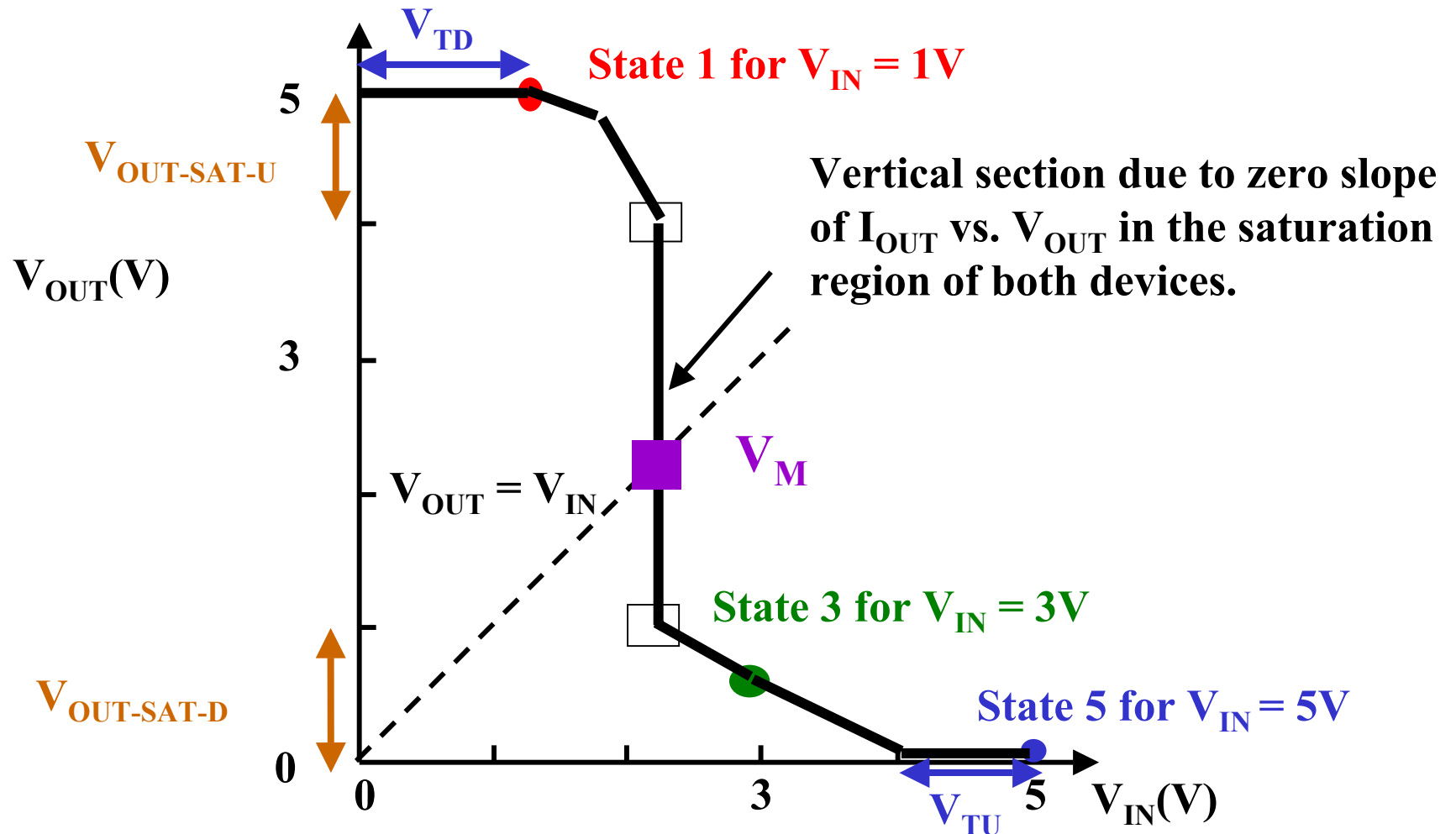
$$I_{OUT-PD} = 20 \frac{\mu A}{V^2} (5V - 3V - 1V) 1V = 20 \mu A$$



Composite I_{OUT} vs. V_{OUT} for CMOS



Voltage Transfer Function for the Complementary Logic Circuit



Method for Finding V_M

At V_M ,

1) $V_{OUT} = V_{IN} = V_M$

2) Both devices are in saturation

3) $I_{OUT-PD} = I_{OUT-PU}$

$$I_{OUT-PD} = k_D (V_{IN} - V_{TD}) V_{OUT-SAT-D}$$

$$= I_{OUT-PU} = k_U (V_{DD} - V_{IN} - V_{TU}) V_{OUT-SAT-U}$$

Substitute V_M

Solve for V_M

Example Result: When $k_D = k_P$, $V_{OUT-SAT-D} = V_{OUT-SAT-U}$ and $V_{TD} = V_{TU}$, then $V_M = V_{DD}/2$